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Technical Data

Document Number: MRF373A

Rev. 7, 9/2008

### **√RoHS**

# **RF Power Field Effect Transistors**

### N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies from 470 to 860 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common source amplifier applications in 28/32 volt transmitter equipment.

 Typical CW Performance at 860 MHz, 32 Volts, Narrowband Fixture Output Power — 75 Watts Power Gain — 18.2 dB Efficiency — 60%

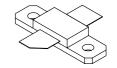
 Capable of Handling 10:1 VSWR @ 32 Vdc, 860 MHz, 75 Watts CW Output Power

#### **Features**

- Integrated ESD Protection
- · Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Low Gold Plating Thickness on Leads.
   L Suffix Indicates 40μ" Nominal.
- RoHS Compliant
- In Tape and Reel. R1 = 500 units per 32 mm, 13 inch Reel.

## MRF373ALR1 MRF373ALSR1

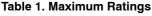
470-860 MHz, 75 W, 32 V LATERAL N-CHANNEL BROADBAND RF POWER MOSFETs



CASE 360B-05, STYLE 1 NI-360 MRF373ALR1



CASE 360C-05, STYLE 1 NI-360S MRF373ALSR1



Rating		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	-0.5, +70	Vdc
Gate-Source Voltage		$V_{GS}$	-0.5, +15	Vdc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	MRF373ALR1 MRF373ALSR1	P <sub>D</sub>	197 1.12 278 1.59	W W/°C W W/°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C
Case Operating Temperature		T <sub>C</sub>	150	°C
Operating Junction Temperature		TJ	200	°C

#### **Table 2. Thermal Characteristics**

Characteristic			Value	Unit
Thermal Resistance, Junction to Case	MRF373ALR1 MRF373ALSR1	$R_{ heta JC}$	0.89 0.63	°C/W

#### **Table 3. ESD Protection Characteristics**

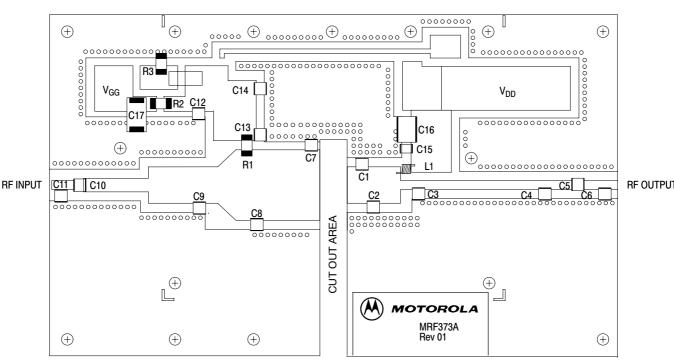
Test Conditions		Class
Human Body Model		1 (Minimum)
Machine Model	MRF373ALR1 MRF373ALSR1	M2 (Minimum) M1 (Minimum)



Table 4. Electrical Characteristics (T<sub>C</sub> = 25°C unless otherwise noted

Characteristic	Symbol	Min	Тур	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage $(V_{GS} = 0 \text{ Vdc}, I_D = 1  \mu\text{A})$	V <sub>(BR)DSS</sub>	70	_	_	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 32 Vdc, V <sub>GS</sub> = 0 Vdc)	I <sub>DSS</sub>	_	_	1	μAdc
Gate-Source Leakage Current (V <sub>GS</sub> = 5 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	_	_	1	μAdc
On Characteristics	•				
Gate Threshold Voltage ( $V_{DS} = 10 \text{ V}, I_D = 200 \mu\text{A}$ )	V <sub>GS(th)</sub>	2	2.9	4	Vdc
Gate Quiescent Voltage (V <sub>DS</sub> = 32 V, I <sub>D</sub> = 100 mA)	V <sub>GS(Q)</sub>	2.5	3.3	4.5	Vdc
Drain-Source On-Voltage (V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A)	V <sub>DS(on)</sub>	_	0.41	0.45	Vdc
Dynamic Characteristics					
Input Capacitance $(V_{DS} = 32 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz})$	C <sub>iss</sub>	_	98.5	_	pF
Output Capacitance $(V_{DS} = 32 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz})$	C <sub>oss</sub>	_	49	_	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 32 V, V <sub>GS</sub> = 0, f = 1 MHz)	C <sub>rss</sub>	_	2	_	pF
functional Characteristics (50 ohm system)					
Common Source Power Gain (V <sub>DD</sub> = 32 V, P <sub>out</sub> = 75 W CW, I <sub>DQ</sub> = 200 mA, f = 860 MHz)	G <sub>ps</sub>	16.5	18.2		dB
Drain Efficiency (V <sub>DD</sub> = 32 V, P <sub>out</sub> = 75 W CW, I <sub>DQ</sub> = 200 mA, f = 860 MHz)	η	56	60	_	%





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Figure 1. MRF373ALR1/ALSR1 Narrowband Test Circuit Component Layout

Table 5. MRF373ALR1/ALSR1 Narrowband Test Circuit Component Layout Designations and Values

Designation	Description
C1, C2	18 pF Chip Capacitors
C3	12 pF Chip Capacitor
C4	1.8 pF Chip Capacitor
C5, C10	51 pF Chip Capacitors
C6	0.3 pF Chip Capacitor (Used only on the MRF373AS)
C7	15 pF Chip Capacitor
C8	10 pF Chip Capacitor
C9	2.7 pF Chip Capacitor
C11	0.5 pF Chip Capacitor
C12	1000 pF Chip Capacitor
C13	39 pF Chip Capacitor
C14, C15	470 pF Chip Capacitors
C16	2.2 μF, 100 V Chip Capacitor
C17	10 μF, 35 V Tantalum Capacitor
L1A	12 nH, Coilcraft
R1, R2	390 Ω, 1/2 W Chip Resistors (2010)
R3	1 kΩ, 1/2 W Chip Resistor (2010)
PCB	Arlon GX-0300-55, 30 mils, $\epsilon_{r}$ = 2.55

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#### TYPICAL CHARACTERISTICS

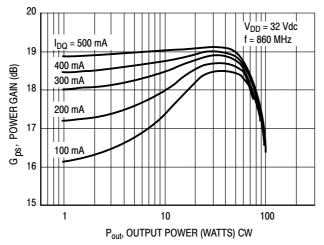


Figure 2. Power Gain versus Output Power

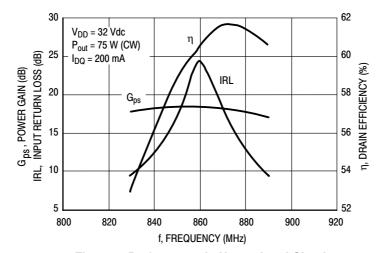


Figure 3. Performance in Narrowband Circuit

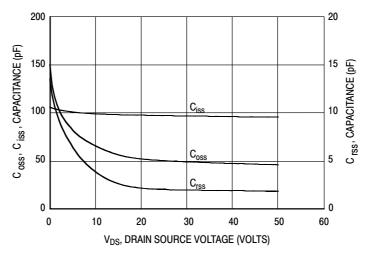
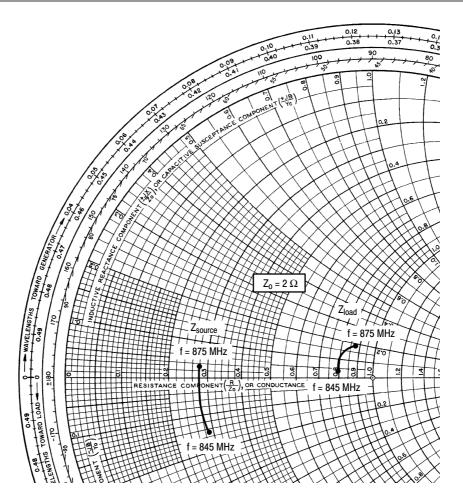


Figure 4. Capacitance versus Voltage



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 $V_{DD}$  = 32 V,  $I_{DQ}$  = 200 mA,  $P_{out}$  = 75 W CW

f MHz	$\begin{array}{c} \mathbf{Z_{source}} \\ \Omega \end{array}$	<b>Z<sub>load</sub></b> Ω
845	0.58 - j0.29	1.60 + j0.07
860	0.56 - j0.11	1.65 + j0.22
875	0.56 + j0.06	1.79 + j0.38

Z<sub>source</sub> = Test circuit impedance as measured from gate to ground.

Z<sub>load</sub> = Test circuit impedance as measured from drain to ground.

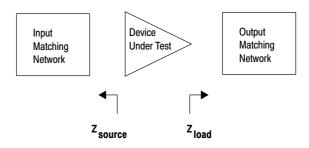
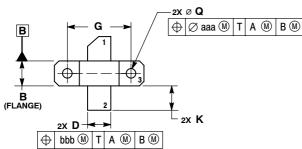


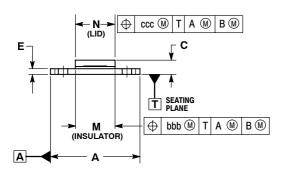
Figure 5. Series Equivalent Source and Load Impedance

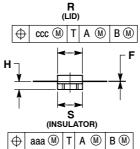
MRF373ALR1 MRF373ALSR1



#### PACKAGE DIMENSIONS







**CASE 360B-05 ISSUE G** NI-360 MRF373ALR1

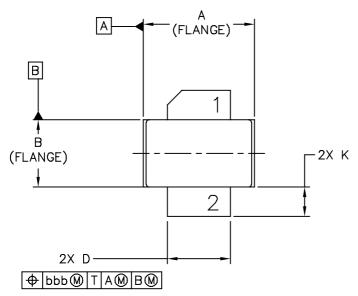
- INTERPRET DIMENSIONS AND TOLERANCES
- 1. INITERPRET DIMENSIONS AND TOLERANCES
  PER ASME Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY
  FROM PACKAGE BODY.

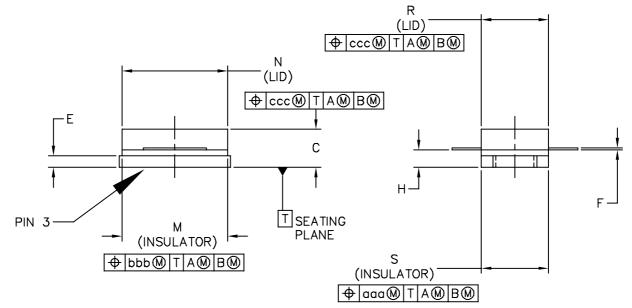
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.795	0.805	20.19	20.45
В	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
Н	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13	REF
bbb	0.010 REF		0.25 REF	
ccc	0.015	REF	0.38	REF

STYLE 1: PIN 1. DRAIN 2. GATE 3. SOURCE



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NI-360S SURFACE MOUNT		CASE NUMBER	R: 360C-05	10 MAR 2006
JOIN AGE MOONT		STANDARD: NO	N-JEDEC	



### NOTES:

- 1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: INCH
- DIMENSION H IS MEASURED . 030 (0. 762) AWAY FROM PACKAGE BODY

STYLE 1:

PIN 1 - DRAIN

2 - GATE 3 - SOURCE

	INCH MI		MILL	IMETER		INCH		MILLIN	METER
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
Α	.375	.385	9.53	9.78	N	.357	.363	9.07	9.22
В	.225	.235	5.72	5.97	R	.227	.233	5.77	5.92
С	.105	.155	2.67	3.94	S	.225	.235	5.72	5.97
D	.210	.220	5.33	5.59					
Ε	.035	.045	0.89	1.14	aaa		.005	0.	13
F	.004	.006	0.1	0.15	bbb		.010	0.	25
Н	.057	.067	1.45	1.7	ccc		.015	0.	38
K	.085	.115	2.16	2.92					
М	.355	.365	9.02	9.27					
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TITLE:

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STANDARD: NON-JEDEC





#### PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

### **Engineering Bulletins**

• EB212: Using Data Sheet Impedances for RF LDMOS Devices

### **REVISION HISTORY**

The following table summarizes revisions to this document.

Revision	Date	Description
7	Sept. 2008	Replaced Case Outline 360C-05, Issue E with Issue F, p. 7-8.
		Added Product Documentation and Revision History, p. 9

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